

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,037,862 B2
APPLICATION NO. : 09/881408
DATED : May 2, 2006
INVENTOR(S) : Kie Y. Ahn and Leonard Forbes

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page item 56

Pg. 2, col. 1, U.S. PATENT DOCUMENTS –

Please insert the following patents:

--6,013,553	*	1/2000	Wallace et al.
6,348,373	*	2/2002	Ma et al.
6,407,435		6/2002	Ma et al.
6,495,474		12/2002	Rafferty et al.
6,573,160		6/2003	Taylor et al.
6,632,729	*	10/2003	Paton
6,679,996	*	1/2004	Yao
6,713,846		3/2004	Senzaki
6,784,508	*	8/2004	Tsunashima et al.
2002/0190302		12/2002	Bojarczuk et al.--

Col. 2, line 24 –

Replace “additional requirements. Thus it would desirable provide”

With --additional requirements. Thus it would be desirable to provide--

Col. 5, line 37 –

Replace “evaporative processes and in particular an electron beam”

With --evaporative process and in particular an electron beam--

Col. 6, line 7 –

Replace “by using a physical deposition (PVD) method as previously”

With --by using a physical vapor deposition (PVD) method as previously--

Col. 7, line 67 –

Replace “oxidation conditions only one effective method and that”

With --oxidation conditions represent only one effective method and that--

Col. 9, line 13 –

Replace “will be understood that the selection of Hf and La form the”

With --will be understood that the selection of Hf and La to form the--

Col. 9, line 36, claim 1 –

Replace “the second layer to temperature effective to form a first”

With --the second layer to a temperature effective to form a first--

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,037,862 B2
APPLICATION NO. : 09/881408
DATED : May 2, 2006
INVENTOR(S) : Kie Y. Ahn and Leonard Forbes

Page 2 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 9, line 61, claim 8 –

Replace “heating to a temperature from about 200° C. to about 400 C.”

With --heating to a temperature from about 200° C. to about 400° C.--

Col. 10, line 42, claim 17 –

Replace “heating the metal lever and layer of silicon dioxide to a”

With --heating the metal layer and layer of silicon dioxide to a--

Col. 10, line 47, claim 17 –

Replace “dielectric lever over the surface, all the metal of the first”

With --dielectric layer over the surface, all the metal of the first--

Col. 11, line 17, claim 22 –

Replace “heating to a temperature from about 200° C. to about 200°”

With --heating to a temperature from about 200° C. to about 400°--

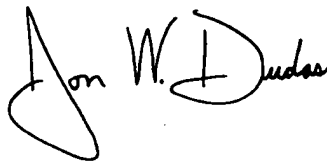
Col. 12, lines 15-16, claim 23 –

Replace “the raction chamber and heating the hafnium-containing”

With --the reaction chamber and heating the hafnium-containing--

Signed and Sealed this

Twenty-fifth Day of November, 2008

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a distinct "D".

JON W. DUDAS
Director of the United States Patent and Trademark Office